## **Megasonic Wet Etching System**

Wet Etching System can be used to etch wet anisotropic Si in bulk micromachining. Our system is designed simply and compactly. Especially the addition of the **MEGAONIC** holder can make the characteristics of Si etching be improved remarkably. Our system is adequate for the R&D and proto type production

## **SPECIFICATIONS**

▶ Wafer size: 4, 5, 6 inch

► Etching Solution: KOH, TMAH

► Megasonic Irradiation

Power Range: ~ 30 W/cm<sup>2</sup>

▶ Bath

Etch Bath: PTFE

Circulation Bath: PTFE

► Solution Temperature Max. Temp: 100°C Temp Uniformity: ± 1°C

► Etching Characteristics

Etch Rate :  $\sim$  1 um/min Etch Uniformity :  $\pm$  2%

Average Surface Roughness: less than 70 nm

(minimum: 2 nm)

▶ Solution Circulation: Teflon Circulation Pump

► Frame: 850(W)mmX750(D)mmX800(H)mm

## **APPLICATIONS**

- ► Si Anisotropic Wet Etch
- ▶ PSL, Electroplating
- ▶ V-Groove, U-Groove, Cavity formation
- ▶ Membrane, microchannel formation







